

Appl. No. 09/902,277

CLAIMS

*Sub E17*  
<sup>46</sup>33. A method of forming a bottom-gated thin film transistor comprising the following steps:

*Rule 124*  
forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine containing layer proximate the polycrystalline thin film transistor layer; and

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

<sup>47</sup>34. The method of claim <sup>46</sup>33 wherein the polycrystalline thin film transistor layer comprises silicon.

<sup>48</sup>35. The method of claim <sup>46</sup>33 wherein the forming a fluorine containing layer comprises forming a sacrificial fluorine containing layer over the thin film transistor layer by chemical vapor deposition utilizing  $WF_6$  and  $SiH_4$  precursors.

*Rule 124*  
*D'*  
<sup>49</sup>36. (Amended) The method of claim <sup>48</sup>35 further comprising, after the transferring fluorine, removing the sacrificial layer from over the thin film transistor layer.

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37. ) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine containing layer over the polycrystalline thin film transistor layer;

~~providing a buffering layer intermediate the thin film transistor layer and the fluorine containing layer; and~~

transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.